

InP OMVPE Epitaxial Wafers

Feature

- Excellent uniformity, Precise epitaxial structure(Thickness, Fraction).

Application

- Photo Diode for telecommunication

Standard Specifications

Application		PIN Photo Diode									
Structure		<table border="1"> <tr> <td>③</td> <td>n or p-InP</td> </tr> <tr> <td>②</td> <td>n-InGaAs</td> </tr> <tr> <td>①</td> <td>n-InP</td> </tr> <tr> <td></td> <td>InP Sub.</td> </tr> </table>		③	n or p-InP	②	n-InGaAs	①	n-InP		InP Sub.
③	n or p-InP										
②	n-InGaAs										
①	n-InP										
	InP Sub.										
Epi.	③ C.C.(cm ⁻³) Thickness(μm)	$\leq 1 \times 10^{18}$ 0.1~3									
	② C.C.(cm ⁻³) Thickness(μm) Lattice Mismatch	$\leq 5 \times 10^{18}$ 1~5 $\leq \pm 1.5 \times 10^{-3}$									
	① C.C.(cm ⁻³) Thickness(μm)	$\leq 5 \times 10^{18}$ 1~3									
Sub.	Size	2"φ, 3"φ, 4"φ, 6"φ									
	Thickness(μm)	350~675									
	Type(Dopant)	N(S)	S.I(Fe)								

Other Specifications are available on request.